

Sergey Pushkarev

List of Publications by Year in descending order

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| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 1 | Enhanced terahertz emission from strain-induced InGaAs/InAlAs superlattices. Journal of Applied Physics, 2019, 125, . | 1.1 | 31 |
| 2 | Terahertz-radiation generation and detection in low-temperature-grown GaAs epitaxial films on GaAs (100) and (111)A substrates. Semiconductors, 2017, 51, 503-508. | 0.2 | 15 |
| 3 | Terahertz-radiation generation in low-temperature InGaAs epitaxial films on (100) and (411) InP substrates. Semiconductors, 2017, 51, 310-317. | 0.2 | 13 |
| 4 | Specific features of the photoluminescence of HEMT nanoheterostructures containing a composite InAlAs/InGaAs/InAs/InGaAs/InAlAs quantum well. Semiconductors, 2015, 49, 234-241. | 0.2 | 12 |
| 5 | Improved InGaAs and InGaAs/InAlAs Photoconductive Antennas Based on (111)-Oriented Substrates. Electronics (Switzerland), 2020, 9, 495. | 1.8 | 10 |
| 6 | Interrelation of the construction of the metamorphic InAlAs/InGaAs nanoheterostructures with the InAs content in the active layer of 76%±100% with their surface morphology and electrical properties. Semiconductors, 2011, 45, 1158-1163. | 0.2 | 9 |
| 7 | Maximum drift velocity of electrons in selectively doped InAlAs/InGaAs/InAlAs heterostructures with InAs inserts. Semiconductors, 2013, 47, 372-375. | 0.2 | 9 |
| 8 | Features of the diagnostics of metamorphic InAlAs/InGaAs/InAlAs nanoheterostructures by high-resolution X-ray diffraction in the θ -scanning mode. Semiconductors, 2016, 50, 559-565. | 0.2 | 9 |
| 9 | Study of new designs for the InAlAs metamorphic buffer on GaAs substrates with distributed compensation of elastic deformations. Semiconductors, 2013, 47, 997-1002. | 0.2 | 8 |
| 10 | X-Ray diffractometry of metamorphic nanoheterostructures. Crystallography Reports, 2014, 59, 258-265. | 0.1 | 8 |
| 11 | Photoluminescence studies of In _{0.7} Al _{0.3} As/In _{0.75} Ga _{0.25} As/In _{0.7} Al _{0.3} As metamorphic heterostructures on GaAs substrates. Semiconductors, 2014, 48, 640-648. | 0.2 | 8 |
| 12 | Structural and photoluminescence properties of low-temperature GaAs grown on GaAs(100) and GaAs(111)A substrates. Semiconductors, 2016, 50, 195-203. | 0.2 | 8 |
| 13 | Photoconductive antennas based on epitaxial films In _{0.5} Ga _{0.5} As on GaAs (100) and (111)A substrates with a metamorphic buffer. Laser Physics Letters, 2018, 15, 076201. | 0.6 | 7 |
| 14 | New Structure for Photoconductive Antennas Based on {LTG-GaAs/GaAs:Si} Superlattice on GaAs(111)A Substrate. Crystallography Reports, 2019, 64, 205-211. | 0.1 | 7 |
| 15 | Influence of buffer-layer construction and substrate orientation on the electron mobilities in metamorphic In _{0.7} Al _{0.3} As/In _{0.76} Ga _{0.24} As/In _{0.7} Al _{0.3} As structures on GaAs substrates. Semiconductors, 2015, 49, 921-929. | 0.2 | 6 |
| 16 | Ultrafast carrier dynamics in LT-GaAs doped with Si delta layers. International Journal of Modern Physics B, 2017, 31, 1750195. | 1.0 | 6 |
| 17 | Photoluminescence Studies of Si-Doped Epitaxial GaAs Films Grown on (100)- and (111)A-Oriented GaAs Substrates at Lowered Temperatures. Semiconductors, 2018, 52, 376-382. | 0.2 | 6 |
| 18 | Photoluminescence properties of modulation-doped In _x Al _{1-x} As/In _y Ga _{1-y} As/In _x Al _{1-x} As structures with strained inas and gaas nanoinserts in the quantum well. Semiconductors, 2015, 49, 1207-1217. | 0.2 | 5 |

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|----|---|-----|-----------|
| 19 | Influence of arsenic flow on the crystal structure of epitaxial GaAs grown at low temperatures on GaAs (100) and (111)A substrates. Crystallography Reports, 2017, 62, 82-90. | 0.1 | 5 |
| 20 | X-ray analysis of multilayer In _{0.52} Al _{0.48} As/In _{0.53} Ga _{0.47} As/In _{0.52} Al _{0.48} As HEMT heterostructures with InAs nanoinset in quantum well. Crystallography Reports, 2017, 62, 355-363. | 0.1 | 5 |
| 21 | Electrophysical and structural properties of the composite quantum wells In _{0.52} Al _{0.48} As/In _x Ga _{1-x} As/In _{0.52} Al _{0.48} As with ultrathin InAs inserts. Journal of Materials Research, 2015, 30, 3020-3025. | | |
| 22 | Study of the influence of strained superlattices introduced into a metamorphic buffer on the electrophysical properties and the atomic structure of InAlAs/InGaAs MHEMT heterostructures. Semiconductors, 2013, 47, 532-537. | 0.2 | 4 |
| 23 | Application of photoluminescence spectroscopy to studies of In _{0.38} Al _{0.62} As/In _{0.38} Ga _{0.62} As/GaAs metamorphic nanoheterostructures. Semiconductors, 2014, 48, 883-890. | 0.2 | 4 |
| 24 | Investigation of In _{0.7} Ga _{0.3} As/In _{0.7} Al _{0.3} As metamorphic HEMT- heterostructures by photoluminescence spectroscopy. Journal of Physics: Conference Series, 2014, 541, 012080. | 0.3 | 4 |
| 25 | Structural and electrical properties of InAlAs/InGaAs/InAlAs HEMT heterostructures on InP substrates with InAs inserts in quantum well. Crystallography Reports, 2014, 59, 900-907. | 0.1 | 3 |
| 26 | X-Ray Diffraction Analysis of Features of the Crystal Structure of GaN/Al _{0.32} Ga _{0.68} N HEMT-Heterostructures by the Williamson-Hall Method. Semiconductors, 2018, 52, 734-738. | 0.2 | 3 |
| 27 | Structural and electrical properties of metamorphic nanoheterostructures with a high InAs content (37±100%) grown on GaAs and InP substrates. Crystallography Reports, 2011, 56, 875-879. | 0.1 | 2 |
| 28 | Structural and electrophysical analysis of MHEMT In _{0.70} Al _{0.30} As/In _{0.75} Ga _{0.25} As nanoheterostructures with different strain distributions in metamorphic buffer. Crystallography Reports, 2012, 57, 841-847. | 0.1 | 2 |
| 29 | Electrical and structural characteristics of metamorphic In _{0.38} Al _{0.62} As/In _{0.37} Ga _{0.63} As/In _{0.38} Al _{0.62} As HEMT nanoheterostructures. Crystallography Reports, 2013, 58, 914-919. | 0.1 | 2 |
| 30 | Electrophysical characteristics and structural parameters of metamorphic HEMT nanoheterostructures In _{0.7} Al _{0.3} As/In _{0.7} Ga _{0.3} As/In _{0.7} Al _{0.3} As containing superlattices with different numbers of periods in the metamorphic buffer. Crystallography Reports, 2014, 59, 425-429. | 0.1 | 2 |
| 31 | Electrical and Photoluminescence Studies of {LT-GaAs/GaAs:Si} Superlattices Grown by MBE on (100)- and (111)A-Oriented GaAs Substrates. Semiconductors, 2019, 53, 246-254. | 0.2 | 2 |
| 32 | Structural Characteristics of Epitaxial Low-Temperature Grown {InGaAs/InAlAs} Superlattices on InP(100) and InP(111)A Substrates. Crystallography Reports, 2020, 65, 496-501. | 0.1 | 2 |
| 33 | X-ray Diffraction Analysis of the Structure In _{0.53} Ga _{0.47} As Films Grown on (100) and (111)A GaAs Substrates with a Metamorphic Buffer. Crystallography Reports, 2022, 67, 317-322. | 0.1 | 2 |
| 34 | Effect of GaAs (100) substrate misorientation on the electrical parameters and surface morphology of metamorphic In _{0.7} Al _{0.3} As/In _{0.75} Ga _{0.25} As/In _{0.7} Al _{0.3} As HEMT nanoheterostructures. Semiconductors, 2014, 48, 63-68. | 0.2 | 1 |
| 35 | Structural and electrophysical properties of In _{0.52} Al _{0.48} As/In _{0.53} Ga _{0.47} As/In _{0.52} Al _{0.48} As/InP HEMT nanoheterostructures with different combinations of InAs and GaAs inserts in quantum well. Crystallography Reports, 2015, 60, 397-405. | 0.1 | 1 |
| 36 | High-resolution X-ray diffractometry and transmission electron microscopy as applied to the structural study of InAlAs/InGaAs/InAlAs multilayer transistor nanoheterostructures. Journal of Surface Investigation, 2016, 10, 495-509. | 0.1 | 1 |

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|----|---|-----|-----------|
| 37 | Epitaxial low-temperature growth of In _{0.5} Ga _{0.5} As films on GaAs(100) and GaAs(111)A substrates using a metamorphic buffer. Crystallography Reports, 2017, 62, 947-954. | 0.1 | 1 |
| 38 | Study of the Surface Morphology, Electrophysical Characteristics, and Photoluminescence Spectra of GaAs Epitaxial Films on GaAs(110) Substrates. Optics and Spectroscopy (English Translation of) Tj ETQq0 0 0 rg012/Overlock 10 Tf 50 | 0.1 | 0 |
| 39 | Silicon-Doped Epitaxial Films Grown on GaAs(110) Substrates: the Surface Morphology, Electrical Characteristics, and Photoluminescence Spectra. Semiconductors, 2020, 54, 1417-1423. | 0.2 | 1 |
| 40 | Influence of metamorphic buffer design on electrophysical and structural properties of MHEMT nanoheterostructures In _{0.7} Al _{0.3} As/In _{0.7} Ga _{0.3} As/In _{0.7} Al _{0.3} As/GaAs. Proceedings of SPIE, 2013, , . | 0.8 | 0 |
| 41 | Generation of THz radiation in epitaxial InGaAs films on InP substates of various crystallographic orientations. , 2016, , . | | 0 |
| 42 | Low-Temperature epitaxial growth of InGaAs films on InP(100) and InP(411)A substrates. Crystallography Reports, 2017, 62, 589-596. | 0.1 | 0 |
| 43 | Electron properties of surface InGaAs/InAlAs quantum wells with inverted doping on InP substrates. Semiconductors, 2017, 51, 760-765. | 0.2 | 0 |
| 44 | Photoconductive antennas based on epitaxial films In _{0.5} Ga _{0.5} As on GaAs (111)A and (100) substrates with a metamorphic buffer. Laser Physics, 2018, 28, 076206. | 0.6 | 0 |